

L Number	Hits	Search Text	DB	Time stamp
5	1105	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/13 12:47
6	452	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant) ) and (selective or selectivity)	USPAT	2004/02/13 12:48
7	443	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant) ) and (selective or selectivity)) and @ay<=2001	USPAT	2004/02/13 12:49
8	196	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant) ) and (selective or selectivity)) and @ay<=2001) and (anneal or annealing)	USPAT	2004/02/13 12:49
9	160	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/13 12:50
10	685	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) not (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))) and @py<=2001) and (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/13 12:51
11	301	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant)) and (etch or etching) and @ay<=2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/13 12:52
12	3	Trapp-Shane-J.in.	USPAT	2004/02/13 13:06
13	10	Trapp-Shane-J.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/13 13:06

14	3	Lawlor-Brian-F.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT	2004/02/13 13:06
-	1	4514251.pn.	USPAT	2003/12/01 13:41
-	1044	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)	USPAT	2004/02/13 12:47
-	835	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)	USPAT	2003/12/01 14:47
-	779	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)	USPAT	2003/12/01 14:47
-	546	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)) and (selective or selectively or selectivity)	USPAT	2003/12/01 13:46
-	208	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)) and ((selective or selectively or selectivity) with (nitride or SiN or "Si.sub.3 N.sub.4"))	USPAT	2003/12/01 14:39
-	147	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)	USPAT	2004/02/13 12:49
-	103	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)	USPAT	2003/12/01 14:47
-	94	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2)	USPAT	2003/12/01 14:47
-	1391	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity)	USPAT	2003/12/01 15:27

-	1090	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant)	USPAT	2003/12/01 15:26
-	405	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)	USPAT	2003/12/01 16:40
-	398	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001	USPAT	2003/12/01 15:27
-	386	(((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))	USPAT	2003/12/01 15:27
-	368	(((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching)	USPAT	2003/12/01 15:27
-	237	(((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))	USPAT	2003/12/01 15:29

-	195	(((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))) and @py<=2001	USPAT	2003/12/01 16:40
-	134	(((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001) not (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001 and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))) and @py<=2001) and (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2"))	USPAT	2004/02/13 13:06
-	431	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)	USPAT	2003/12/02 15:52
-	307	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant)	USPAT	2003/12/02 10:01
-	282	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant)) and (etch or etching) and @ay<=2001	USPAT	2004/02/13 12:52

-	167	(((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting or implantation or dope or doped or doping or dopant)) and (etch or etching) and @ay<=2001) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (al! or aluminum or Ga or gallium or boron or B!))	USPAT	2003/12/02 15:36
-	21	("3886569"   "4806199"   "4807016"   "5275972"   "5286344"   "5300463"   "5424570"   "5468342"   "5562801"   "5626716"   "5695658"   "5759888"   "5814563"   "5817580"   "5841195"   "5843845"   "5843847"   "5855962"   "5965035"   "6051870"   "6239017").PN.	USPAT	2003/12/02 12:08
-	290	438/705.ccls.	USPAT	2003/12/02 15:36
-	650	438/706.ccls.	USPAT	2003/12/02 15:36
-	118	348/714.ccls.	USPAT	2003/12/02 15:36
-	729	438/723.ccls.	USPAT	2003/12/02 15:36
-	393	438/724.ccls.	USPAT	2003/12/02 15:37
-	38	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)	US-PGPUB; EPO; JPO; DERWENT	2004/02/13 12:51